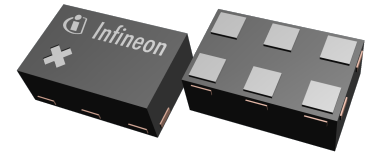


BGA535N6

Broadband low power LNA for L1/L2/L5 GNSS applications

Features

- Operation frequencies 1164 to 1615 MHz
- Multiple operating modes for different applications
- Current consumption down to 1.5 mA
- Wide supply voltage range 1.1 V to 3.3 V
- High insertion power gain up to 18 dB
- Low noise figure down to 0.7 dB
- 2 kV HBM ESD protection (including AI pin)
- Broadband design provides best sensitivity for GNSS signals within 1164 to 1615 MHz with the same matching
- extended temperature range -40...105 °C



- RoHS
- Halogen-Free
- Lead-Free
- Green

Potential application

BGA535N6 enhances GNSS signal sensitivity for band L1/L2/L5 especially in wearables and industrial applications. It offers 2 different operating modes:

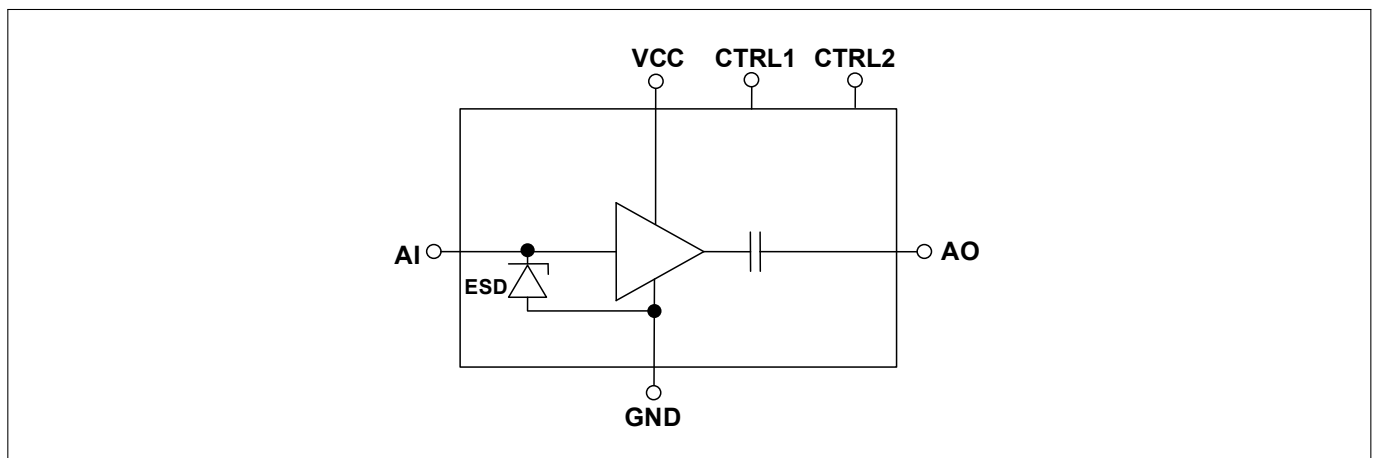
- Low power mode
- Standard mode

The broadband design provides best sensitivity for GNSS signals within 1164 to 1615 MHz with the same matching. Simplified dual-band GNSS system designs with one RF-path are enabled by BGA535N6.

Product validation

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22.

Block diagram



Product Name	Marking	Package	Ordering Information
BGA535N6	9	PG-TSNP-6-10	BGA535N6 E6327

BGA535N6

Broadband low power LNA for L1/L2/L5 GNSS applications

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BGA535N6

Broadband low power LNA for L1/L2/L5 GNSS applications

Absolute maximum ratings

1 Absolute maximum ratings

Table 1: Absolute maximum ratings

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Voltage at pin VCC	V_{CC}	-0.3	–	3.6	V	¹
Voltage at pin AI	V_{AI}	–	–	–	V	²
Voltage at pin AO	V_{AO}	-0.3	–	$V_{CC} + 0.3$	V	$V_{CC} + 0.3$ must not exceed 3.6 V
Voltage at pin CTRL1/CTRL2	V_{CTRL}	-0.3	–	$V_{CC} + 0.3$	V	–
Current into pin VCC	I_{CC}	–	–	10	mA	–
Junction temperature	T_J	–	–	125	°C	–
Ambient temperature range	T_A	-40	–	105	°C	–
Storage temperature range	T_{STG}	-55	–	150	°C	–
ESD capability, HBM	V_{ESD_HBM}	-2000	–	+2000	V	³
ESD capability, CDM	V_{ESD_CDM}	-1000	–	+1000	V	⁴
RF input power	P_{IN}	–	–	+25	dBm	CW signal, VSWR 10:1, (refer to 50 Ohm), device level, VCC/VCTRL type, 25 °C, for 30s and all modes.

¹All voltages refer to GND-Nodes unless otherwise noted

²No external DC Voltage allowed

³Human Body Model ANSI/ESDA/JEDEC JS-001 ($R = 1.5 \text{ k}\Omega$, $C = 100 \text{ pF}$)

⁴Field-Induced Charged-Device Model ANSI/ESDA/JEDEC JS-002. Simulates charging/discharging events that occur in production equipment and processes. Potential for CDM ESD events occurs whenever there is metal-to-metal contact in manufacturing.

Warning: Stresses above the max. values listed here may cause permanent damage to the device. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit. Exposure to conditions at or below absolute maximum rating but above the specified maximum operation conditions may affect device reliability and life time. Functionality of the device might not be given under these conditions.

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Broadband low power LNA for L1/L2/L5 GNSS applications

Electrical characteristics

2 Electrical characteristics

Table 2: Operation ranges at $T_A = 25\text{ °C}$, $f = \text{L1/L2/L5}$

Parameter ¹	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Supply voltage	V_{CC}	1.1	–	3.3	V	–
Control input voltage	V_{IH}	$0.7 * V_{CC}$	–	VCC	V	logic H
	V_{IL}	0	–	$0.3 * V_{CC}$	V	logic L
Stability	k	>1	–	–		$f=20\text{ MHz}-10\text{ GHz}$ (all modes)
Transient time	t_s	–	30	32	ns	Low power mode to Off mode Standard mode to Off mode
		–	21.7	23.5	μs	C1=1nF Off to Low power mode Off to standard mode
		–	733	847	ns	C1=10pF Off to Low power mode Off to standard mode

¹Based on application described in chapter 3

BGA535N6

Broadband low power LNA for L1/L2/L5 GNSS applications

Electrical characteristics

Table 3: Electrical characteristics at $T_A = 25\text{ }^\circ\text{C}$, Low power mode, $f = 1164\text{--}1300\text{ MHz}$

Parameter ¹	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Supply current	I_{CC}	-	1.5	1.8	mA	Low power mode, VCC=1.8V
		-	-	1	μA	Off mode
Insertion power gain ¹ $f = 1176\text{ MHz}$	$ S_{21} ^2$	14.5	15.5	16.5	dB	VCC=1.2V
		14.5	15.5	16.5	dB	VCC=1.8V
		14.5	15.5	16.5	dB	VCC=2.8V
Noise figure ² $f = 1176\text{ MHz}$	NF	-	0.9	1.2	dB	VCC=1.2V
		-	0.9	1.2	dB	VCC=1.8V
		-	0.9	1.2	dB	VCC=2.8V
Input return loss ³ $f = 1176\text{ MHz}$	RL_{IN}	8	9.5	-	dB	VCC=1.2V
		7.5	9	-	dB	VCC=1.8V
		7.5	9	-	dB	VCC=2.8V
Output return loss ³ $f = 1176\text{ MHz}$	RL_{OUT}	9	11	-	dB	VCC=1.2V
		9	11	-	dB	VCC=1.8V
		9	11	-	dB	VCC=2.8V
Reverse isolation ³ $f = 1176\text{ MHz}$	$1/ S_{12} ^2$	30	33	-	dB	VCC=1.2V
		30	34	-	dB	VCC=1.8V
		30	34	-	dB	VCC=2.8V
Inband input 1dB-compression point ³ $f = 1176\text{ MHz}$	IP_{1dB}	-17	-14	-	dBm	VCC=1.2V
		-13	-10	-	dBm	VCC=1.8V
		-9	-6	-	dBm	VCC=2.8V
Out of band input 3rd-order intercept point ³	IIP_{300B}	-7	-4.5	-	dBm	VCC=1.2V, $f_1 = 1785\text{ MHz}, f_2 = 2401\text{ MHz},$ $P_1=P_2=-20\text{ dBm}$
		-7.5	-5	-	dBm	VCC=1.8V, $f_1 = 1785\text{ MHz}, f_2 = 2401\text{ MHz},$ $P_1=P_2=-20\text{ dBm}$
		-8	-5.5	-	dBm	VCC=2.8V, $f_1 = 1785\text{ MHz}, f_2 = 2401\text{ MHz},$ $P_1=P_2=-20\text{ dBm}$

¹Based on application described in chapter 3

²PCB losses are subtracted

³Verification based on AQL; not 100% tested in production

Electrical characteristics

Table 4: Electrical characteristics at $T_A = 25\text{ °C}$, Standard mode, $f = 1164\text{--}1300\text{ MHz}$

Parameter ¹	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Supply current	I_{CC}	-	2.3	2.4	mA	Standard mode, VCC=1.8V
		-	-	1	μA	Off mode
Insertion power gain ¹ $f = 1176\text{ MHz}$	$ S_{21} ^2$	16.8	17.8	18.8	dB	VCC=1.2V
		16.8	17.9	18.8	dB	VCC=1.8V
		16.8	17.8	18.8	dB	VCC=2.8V
Noise figure ² $f = 1176\text{ MHz}$	NF	-	0.8	1.1	dB	VCC=1.2V
		-	0.8	1.1	dB	VCC=1.8V
		-	0.8	1.1	dB	VCC=2.8V
Input return loss ³ $f = 1176\text{ MHz}$	RL_{IN}	8	11	-	dB	VCC=1.2V
		7.5	10.5	-	dB	VCC=1.8V
		7.5	10.5	-	dB	VCC=2.8V
Output return loss ³ $f = 1176\text{ MHz}$	RL_{OUT}	9	11	-	dB	VCC=1.2V
		9	11	-	dB	VCC=1.8V
		9	11	-	dB	VCC=2.8V
Reverse isolation ³ $f = 1176\text{ MHz}$	$1/ S_{12} ^2$	30	34	-	dB	VCC=1.2V
		30	34	-	dB	VCC=1.8V
		30	34	-	dB	VCC=2.8V
Inband input 1dB-compression point ³ $f = 1176\text{ MHz}$	IP_{1dB}	-19	-16.5	-	dBm	VCC=1.2V
		-15	-12	-	dBm	VCC=1.8V
		-11	-8.5	-	dBm	VCC=2.8V
Out of band input 3rd-order intercept point ³	IIP_{300B}	-2	0.5	-	dBm	VCC=1.2V, $f_1 = 1785\text{ MHz}, f_2 = 2401\text{ MHz},$ $P_1=P_2=-20\text{ dBm}$
		-5	-2.5	-	dBm	VCC=1.8V, $f_1 = 1785\text{ MHz}, f_2 = 2401\text{ MHz},$ $P_1=P_2=-20\text{ dBm}$
		-5	-2.5	-	dBm	VCC=2.8V, $f_1 = 1785\text{ MHz}, f_2 = 2401\text{ MHz},$ $P_1=P_2=-20\text{ dBm}$

¹Based on application described in chapter 3

²PCB losses are subtracted

³Verification based on AQL; not 100% tested in production

BGA535N6

Broadband low power LNA for L1/L2/L5 GNSS applications

Electrical characteristics

Table 5: Electrical characteristics at $T_A = 25\text{ °C}$, Low power mode, $f = 1550\text{--}1615\text{ MHz}$

Parameter ¹	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Supply current	I_{CC}	-	1.5	1.8	mA	Low power mode, VCC=1.8V
		-	-	1	μA	Off mode
Insertion power gain ¹ $f = 1575\text{ MHz}$	$ S_{21} ^2$	13	14	15	dB	VCC=1.2V
		13.5	14.5	15.5	dB	VCC=1.8V
		14	15	16	dB	VCC=2.8V
Noise figure ² $f = 1575\text{ MHz}$	NF	-	1	1.3	dB	VCC=1.2V
		-	1	1.3	dB	VCC=1.8V
		-	1	1.3	dB	VCC=2.8V
Input return loss ³ $f = 1575\text{ MHz}$	RL_{IN}	8.5	11.5	-	dB	VCC=1.2V
		10.5	13.7	-	dB	VCC=1.8V
		11	14	-	dB	VCC=2.8V
Output return loss ³ $f = 1575\text{ MHz}$	RL_{OUT}	11	13	-	dB	VCC=1.2V
		11.5	13.5	-	dB	VCC=1.8V
		12	14	-	dB	VCC=2.8V
Reverse isolation ³ $f = 1575\text{ MHz}$	$1/ S_{12} ^2$	30	36	-	dB	VCC=1.2V
		30	36	-	dB	VCC=1.8V
		30	36	-	dB	VCC=2.8V
Inband input 1dB-compression point ³ $f = 1575\text{ MHz}$	IP_{1dB}	-14	-12	-	dBm	VCC=1.2V
		-10.5	-8.5	-	dBm	VCC=1.8V
		-6.5	-4.5	-	dBm	VCC=2.8V
Out of band input 3rd-order intercept point ³	IIP_{300B}	-7.5	-5	-	dBm	VCC=1.2V, $f_1 = 1713\text{ MHz}, f_2 = 1850\text{ MHz},$ $P_1=P_2=-20\text{ dBm}$
		-10	-7.5	-	dBm	VCC=1.8V, $f_1 = 1713\text{ MHz}, f_2 = 1850\text{ MHz},$ $P_1=P_2=-20\text{ dBm}$
		-11	-8.5	-	dBm	VCC=2.8V, $f_1 = 1713\text{ MHz}, f_2 = 1850\text{ MHz},$ $P_1=P_2=-20\text{ dBm}$

¹Based on application described in chapter 3

²PCB losses are subtracted

³Verification based on AQL; not 100% tested in production

Electrical characteristics

Table 6: Electrical characteristics at $T_A = 25\text{ }^\circ\text{C}$, Standard mode, $f = 1550\text{--}1615\text{ MHz}$

Parameter ¹	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Supply current	I_{CC}	-	2.3	2.4	mA	Standard mode, VCC=1.8V
		-	-	1	μA	Off Mode
Insertion power gain ¹ $f = 1575\text{ MHz}$	$ S_{21} ^2$	15.5	16.5	17.5	dB	VCC=1.2V
		16	17	18	dB	VCC=1.8V
		16	17	18	dB	VCC=2.8V
Noise figure ² $f = 1575\text{ MHz}$	NF	-	0.85	1.15	dB	VCC=1.2V
		-	0.85	1.15	dB	VCC=1.8V
		-	0.85	1.15	dB	VCC=2.8V
Input return loss ³ $f = 1575\text{ MHz}$	RL_{IN}	15.5	18.5	-	dB	VCC=1.2V
		16.5	19	-	dB	VCC=1.8V
		16.5	19	-	dB	VCC=2.8V
Output return loss ³ $f = 1575\text{ MHz}$	RL_{OUT}	11	13	-	dB	VCC=1.2V
		11.5	13.5	-	dB	VCC=1.8V
		12	14	-	dB	VCC=2.8V
Reverse isolation ³ $f = 1575\text{ MHz}$	$1/ S_{12} ^2$	30	35	-	dB	VCC=1.2V
		30	35	-	dB	VCC=1.8V
		30	35	-	dB	VCC=2.8V
Inband input 1dB-compression point ³ $f = 1575\text{ MHz}$	IP_{1dB}	-17	-15	-	dBm	VCC=1.2V
		-13	-11	-	dBm	VCC=1.8V
		-9	-6.7	-	dBm	VCC=2.8V
Out of band input 3rd-order intercept point ³	IIP_{300B}	-7.5	-5	-	dBm	VCC=1.2V, $f_1 = 1713\text{ MHz}, f_2 = 1850\text{ MHz},$ $P_1=P_2=-20\text{ dBm}$
		-5.5	-3	-	dBm	VCC=1.8V, $f_1 = 1713\text{ MHz}, f_2 = 1850\text{ MHz},$ $P_1=P_2=-20\text{ dBm}$
		-7.5	-5	-	dBm	VCC=2.8V, $f_1 = 1713\text{ MHz}, f_2 = 1850\text{ MHz},$ $P_1=P_2=-20\text{ dBm}$

¹Based on application described in chapter 3

²PCB losses are subtracted

³Verification based on AQL; not 100% tested in production

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Application information

3 Application information

Pin configuration and function

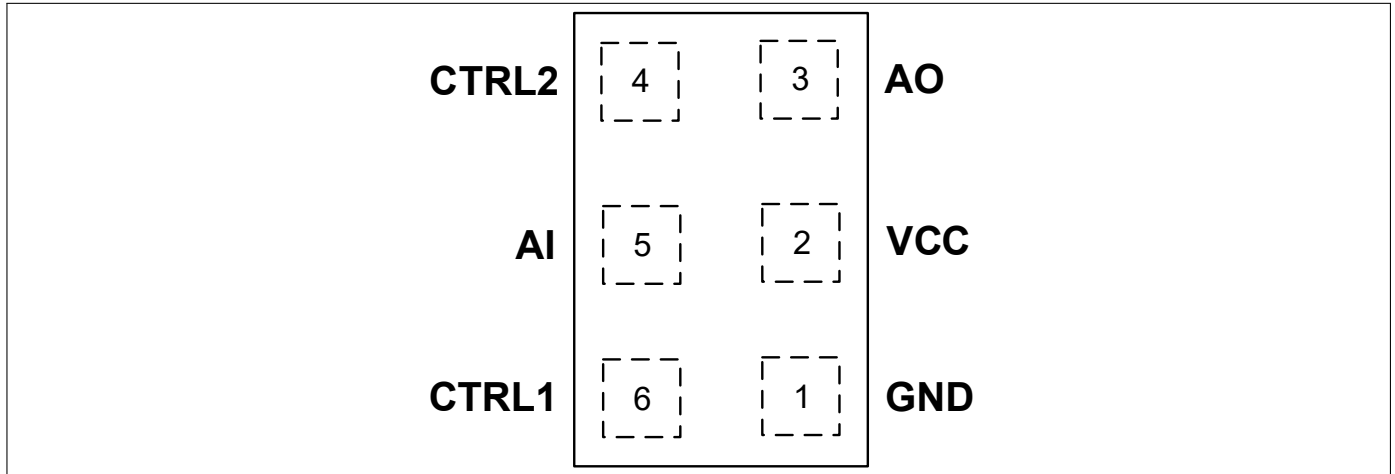


Figure 1: BGA535N6 pin configuration (top view)

Table 7: Pin definition and function

Pin No.	Name	Function
1	GND	Ground
2	VCC	DC supply
3	AO	LNA output
4	CTRL2	Control pin 2
5	AI	LNA input
6	CTRL1	Control pin 1

Table 8: Gain mode selection truth table

Control voltage V_{CTRL1}	Control voltage V_{CTRL2}	Gain mode
High	Low	Standard mode
High	High	Low power mode
Low	Low	Off mode

BGA535N6

Broadband low power LNA for L1/L2/L5 GNSS applications

Application information

Application board configuration

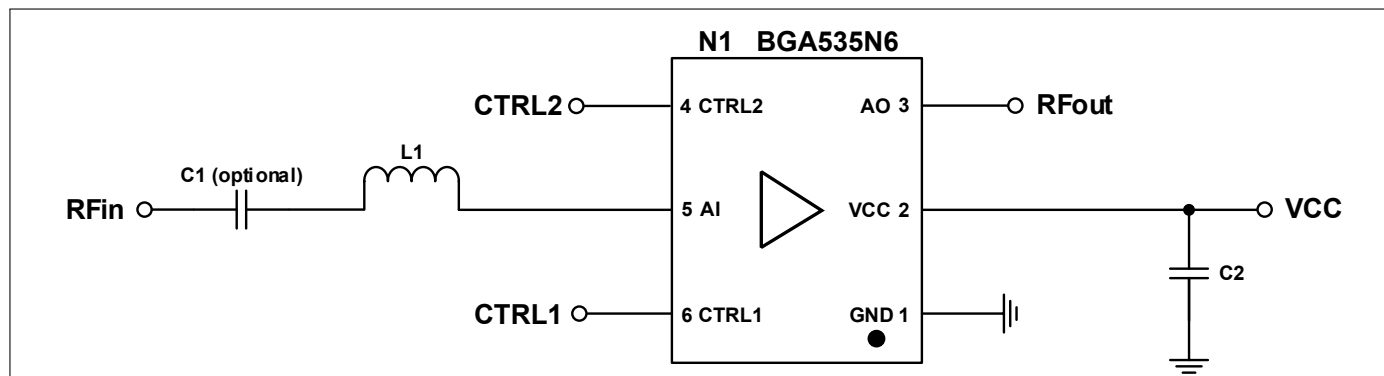


Figure 2: BGA535N6 Application schematic for L1/L2/L5

Table 9: Bill of materials table

Name	Value	Package	Manufacturer	Function
C1	1nF	0402	Various	DC block
C2	68pF	0402	Various	bypass
L1	see matching table	0402	Murata LQW15 type	Input matching
N1	BGA535N6	PG-TSNP-6-10	Infineon Technologies	GNSS LNA

Table 10: Matching table

Band	Operation mode	Matching inductor
L1 & L2/L5	Low power - 1.5mA	12 nH
	Standard - 2.3mA	11 nH

BGA535N6

Broadband low power LNA for L1/L2/L5 GNSS applications

Package information

4 Package information

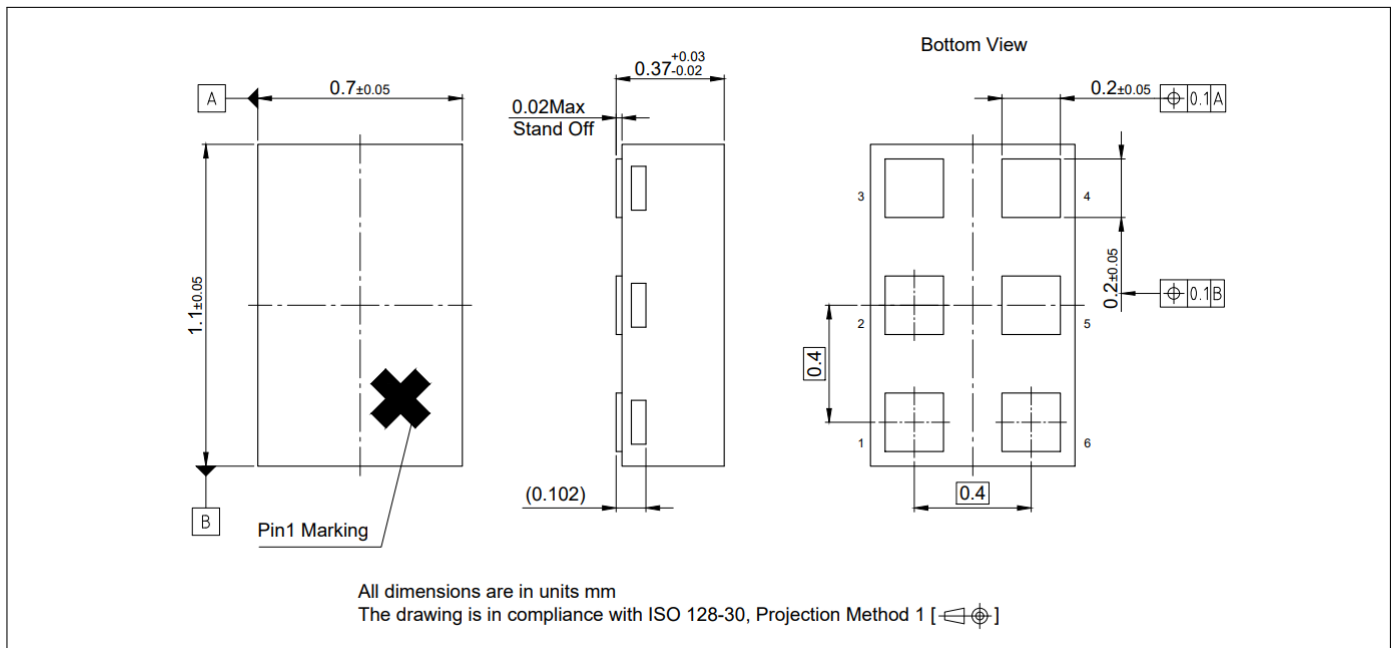


Figure 3: PG-TSNP-6-10 package outline (0.7mm x 1.1mm x 0.37mm)

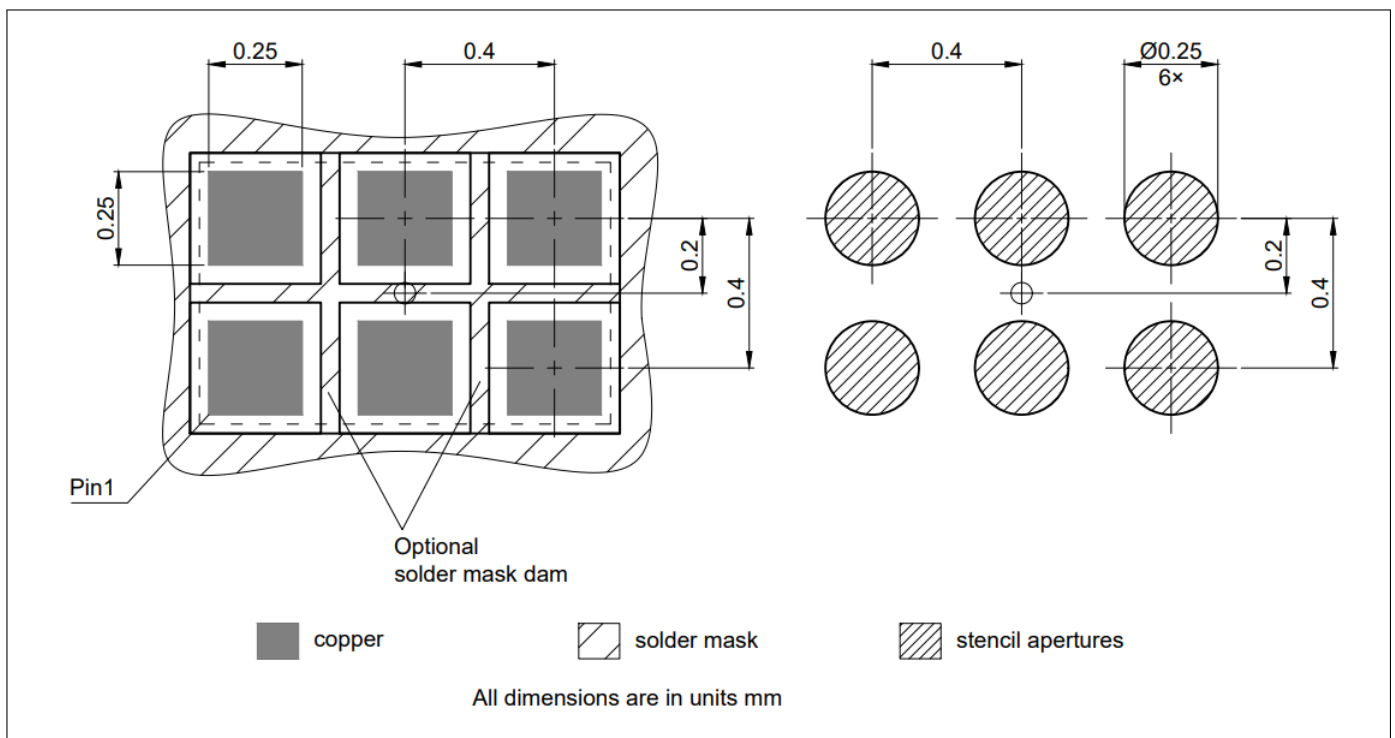


Figure 4: Footprint recommendation

BGA535N6

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Package information

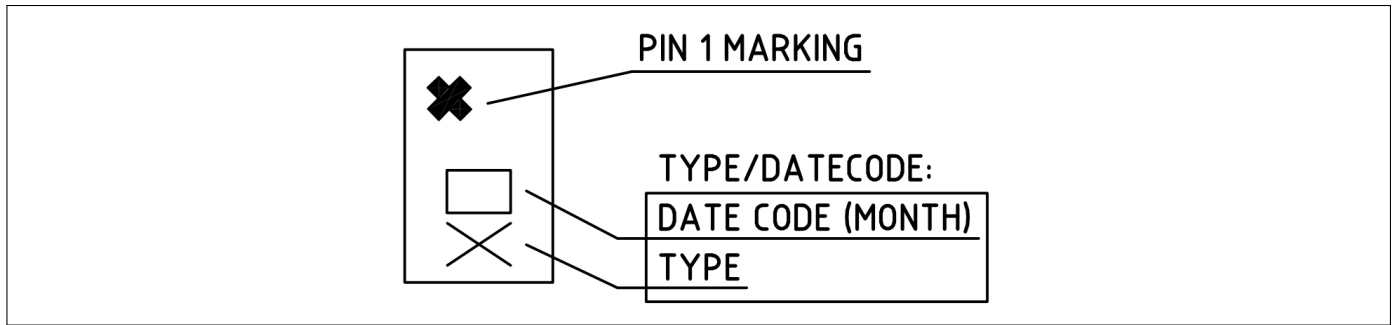


Figure 5: Marking specification (top view)

Table 11: Monthly date code marking

Month	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026
1	a	p	A	P	a	p	A	P	a	p	A	P
2	b	q	B	Q	b	q	B	Q	b	q	B	Q
3	c	r	C	R	c	r	C	R	c	r	C	R
4	d	s	D	S	d	s	D	S	d	s	D	S
5	e	t	E	T	e	t	E	T	e	t	E	T
6	f	u	F	U	f	u	F	U	f	u	F	U
7	g	v	G	V	g	v	G	V	g	v	G	V
8	h	x	H	X	h	x	H	X	h	x	H	X
9	j	y	J	Y	j	y	J	Y	j	y	J	Y
10	k	z	K	Z	k	z	K	Z	k	z	K	Z
11	l	2	L	4	l	2	L	4	l	2	L	4
12	n	3	N	5	n	3	N	5	n	3	N	5

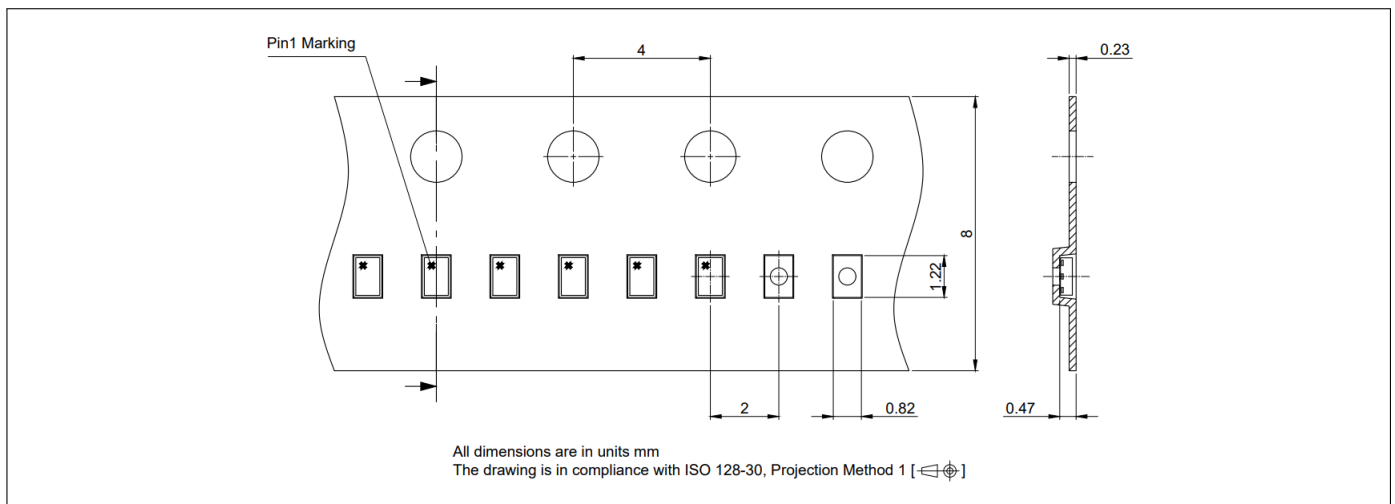


Figure 6: PG-TSNP-6-10 carrier tape

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Broadband low power LNA for L1/L2/L5 GNSS applications



Revision history

-

Page or item	Subjects (major changes since previous revision)
Revision 1.4, 2025-07-14	

Revision history

	Test conditions typos corrected

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